L Number	Hits	Search Text	DB	Time stamp
-	49	((oxide adj film) near10 (apart or separate	USPAT;	2004/03/05
		or separated or separation or separating or	US-PGPUB;	18:02
		isolate or isolated) near10 surface near10	EPO; JPO;	. –
		(semiconductor adj substrate)).clm.	DERWENT;	
			IBM_TDB	
_	17	((oxide adj film) near10 (apart or separate	USPAT;	2004/03/05
•	• •	or separated or separation or separating or	1	18:05
			US-PGPUB;	10:05
		isolate or isolated) near10 ((main or reverse	EPO; JPO;	
		or first or second or upper or lower or	DERWENT;	
		opposite) adj surface) near10	IBM_TDB	
		(semiconductor adj substrate)).clm.		
-	3	((oxide adj film) near10 (apart or separate	USPAT;	2004/03/05
		or separated or separation or separating or	US-PGPUB;	18:06
		isolate or isolated) near10 ((main or reverse	EPO; JPO;	
		or first or second or upper or lower or	DERWENT;	
		opposite) adj surface) near10	IBM_TDB	
		(semiconductor adj substrate)).clm. and	_	
		(epitaxy or epitaxially or epitaxial).clm.	:	
_	22	((oxide adj film) near10 (apart or separate	USPAT;	2004/03/05
		or separated or separation or separating or	US-PGPUB;	18:07
		isolate or isolated) near10 ((main or reverse	EPO; JPO;	10:07
		•		
		or first or second or upper or lower or	DERWENT;	
		opposite) adj surface) near10	IBM_TDB	
		(semiconductor adj substrate)) and (epitaxy		
		or epitaxially or epitaxial)		
-	3	((oxide adj film) near10 (apart) near10	USPAT;	2004/03/05
		((main or reverse or first or second or upper	US-PGPUB;	18:12
		or lower or opposite) adj surface) near10	EPO; JPO;	
		(semiconductor adj substrate)) and (epitaxy	DERWENT;	
		or epitaxially or epitaxial)	IBM_TDB	
-	27	((oxide adj film) near10 (apart or between)	USPAT;	2004/03/05
		near10 ((main or reverse or first or second	US-PGPUB;	18:15
		or upper or lower or opposite) adj surface)	EPO; JPO;	
		near10 (semiconductor adj substrate)) and	DERWENT;	
		(epitaxy or epitaxially or epitaxial)	IBM_TDB	
_	5	((oxide adj film) near10 (apart or between)	USPAT;	2004/03/05
	_	near10 ((main or reverse or first or second	US-PGPUB;	18:20
		or upper or lower or opposite) adj surface)	EPO; JPO;	10.20
		near10 (semiconductor adj substrate)).clm.	DERWENT;	
		•		,
-	5	and (epitaxy or epitaxially or epitaxial).clm.	IBM_TDB	2004/02/05
	ວ	((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
		or buried) near10 ((main or reverse or first	US-PGPUB;	18:21
		or second or upper or lower or opposite) adj	EPO; JPO;	
		surface) near10 (semiconductor adj	DERWENT;	
		substrate)).clm. and (epitaxy or epitaxially	IBM_TDB	
		or epitaxial).clm.		

-	2	((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
		or buried) near10 ((main or reverse or first	US-PGPUB;	18:21
		or second or upper or lower or opposite) adj	EPO; JPO;	
		surface) near10 (semiconductor adj	DERWENT;	
		substrate)).clm. same (epitaxy or	IBM_TDB	
		epitaxially or epitaxial).clm.		
-	5	((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
		or buried) near10 ((main or reverse or first	US-PGPUB;	18:23
		or second or upper or lower or opposite) adj	EPO; JPO;	
		surface) near10 (semiconductor adj	DERWENT;	
		substrate)) same (epitaxy or epitaxially or	IBM_TDB	
		epitaxial)	_	
-	84	((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
		or buried) near10 (semiconductor adj	US-PGPUB;	18:24
		substrate)) same (epitaxy or epitaxially or	EPO; JPO;	
		epitaxial)	DERWENT;	
			IBM_TDB	
_	6	(((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
		or buried) near10 (semiconductor adj	US-PGPUB;	18:26
		substrate)) same (epitaxy or epitaxially or	EPO; JPO;	
		epitaxial)).clm.	DERWENT;	
			IBM_TDB	
_	5	(((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
		or buried) near10 (semiconductor adj	US-PGPUB;	18:29
	ļ	substrate)) same ((epitaxy or epitaxially or	EPO; JPO;	10.20
		epitaxial) near layer)).clm.	DERWENT;	
		opicasiai, iioai iajoi,,,ioiiiii	IBM_TDB	
_	59	(((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
	1	or buried) near10 (semiconductor adj	US-PGPUB;	18:30
		substrate)) same ((epitaxy or epitaxially or	EPO; JPO;	10.00
		epitaxial) near layer))	DERWENT;	
		opitaxial, liour layor,,	IBM_TDB	
_	18	(((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
		or buried) near10 (semiconductor adj	US-PGPUB;	18:31
		substrate)) same ((epitaxy or epitaxially or	EPO; JPO;	10.01
		epitaxial) near layer)) and ((epitaxy or	DERWENT;	
		epitaxially or epitaxial) near layer).clm.	IBM_TDB	
l <u>.</u>	15	(((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
-	"	or buried) near10 (semiconductor adj	US-PGPUB;	18:31
		substrate)) same ((epitaxy or epitaxially or	EPO; JPO;	13.31
		epitaxial) near layer)) and ((epitaxy or	DERWENT;	
		epitaxial) near layer)) and ((epitaxy or epitaxially or epitaxial) near layer).clm. and	· .	
		(oxide near film).clm.	IBM_TDB	
l <u>.</u>	15	(oxide near film).cim. (((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
-	13	or buried) near10 (semiconductor adj	US-PGPUB;	
				18:31
		substrate)) same ((epitaxy or epitaxially or	EPO; JPO;	
		epitaxial) near layer)) and ((epitaxy or	DERWENT;	
		epitaxially or epitaxial) near layer).clm. and	IBM_TDB	
		(oxide adj film).clm.	<u> </u>	

•	8	(((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
		or buried) near10 (semiconductor adj	US-PGPUB;	18:32
	İ	substrate)) same ((epitaxy or epitaxially or	EPO; JPO;	
		epitaxial) near layer)) and ((epitaxy or	DERWENT;	
		epitaxially or epitaxial) near layer).clm. and	IBM_TDB	
		(oxide adj film).clm. and (oxide adj film).ab.		
-	0	(((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
		or buried) near10 (semiconductor adj	US-PGPUB;	18:33
		substrate)) same ((epitaxy or epitaxially or	EPO; JPO;	
		epitaxial) near layer)) and ((epitaxy or	DERWENT;	
		epitaxially or epitaxial) near layer).clm. and	IBM_TDB	
		(oxide adj film).clm. and (oxide adj film).ab.		
		and ((auto near doping) or warpage).clm.		
•	2	(((oxide adj film) near10 (apart or between	USPAT;	2004/03/05
		or buried) near10 (semiconductor adj	US-PGPUB;	18:33
		substrate)) same ((epitaxy or epitaxially or	EPO; JPO;	
		epitaxial) near layer)) and ((epitaxy or	DERWENT;	
		epitaxially or epitaxial) near layer).clm. and	IBM_TDB	
		(oxide adj film).clm. and (oxide adj film).ab.		
		and ((auto near doping) or warpage)		